

ABSTRACT OF THE DISCLOSURE

The photolithography processes for connecting the first conductive film pattern, which is a lower layer such as a gate electrode of a TFT, to a
5 second conductive film pattern, which is an upper layer such as a source/drain electrode of a TFT are reduced by utilizing laminated films and a resist pattern formed thereon having different film thicknesses. Laminated films constituting the
10 source/drain electrode are formed by depositing films on an insulating substrate on which the first conductive film pattern is formed, and the resist pattern is formed on the top layer of the laminated films, and then utilizing the film thickness
15 difference of the resist pattern and the film composition of the laminated films, the short circuited wiring between the gate electrode and the source/drain electrode for an Electro-Static-Discharge protection circuit of the active matrix
20 substrate can be formed by less photolithography processes than that in the manufacturing of the conventional active matrix substrate.